

**AMENDMENTS TO THE SPECIFICATION:**

Page 1, after the title, please insert as follows:

This application is the US national phase of international application PCT/AU03/00048 filed 17 January 2003, which designated the US and claims priority to AU Application No. PS 0011 filed 17 January 2002. The entire contents of these applications are incorporated herein by reference.

Please add the new paragraphs beginning at page 8, after line 23, as follows:

In accordance with a further aspect of the invention, there is provided a method for converting the type of a region of a p-type body to form an n-p junction, comprising reactive ion etching a portion of the surface of a p-type body for a prescribed time period at a prescribed pressure, progressively converting the underlying p-type of the body to n-type to a depth determined by said time period and said pressure.

Preferably, the method includes mounting the p-type body on a cathode of a parallel plate reactor and applying a hydrogen flow rate of 27sccm.

Preferably, the method includes mounting the p-type body on a cathode of a parallel plate reactor and applying a methane flow rate of 5sccm.

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Appl. No. To be assigned

US National Phase of PCT/AU03/00048

July 19, 2004

Preferably, the method includes mounting the p-type body on a cathode of a parallel plate reactor and applying a total pressure of 412mTorr.

Preferably, the method includes mounting the p-type body on a cathode of a parallel plate reactor and applying a DC bias of 200V.

Preferably, the method includes mounting the p-type body on a cathode of a parallel plate reactor and applying a cathode temperature of 18°C.

Preferably, said prescribed time period is 2 minutes to produce a depth of approximately 3 $\mu$ m.